

Abstract of the disclosure

In accordance with embodiments of the present invention a trench-level dielectric film (26) and a via-level dielectric film (24) are formed overlying a semiconductor device substrate (10). A via opening (42) is etched in the trench-level dielectric film with a first etch chemistry that has a higher etch selectivity to the trench-level dielectric film (26) than to the via-level dielectric film (24). A trench opening (54) is patterned in a photoresist layer (52) overlying the trench-level dielectric film (26). The via-level dielectric film (24) is etched with a second etch chemistry to extend the via opening (42) into the via-level dielectric film (24). The trench-level dielectric film (26) is etched to form a trench opening.

(FIG. 7 to accompany abstract)



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